

HEX BUS BUFFER (3-STATE)

The TC74AC367 is an advanced high speed CMOS HEX BUS BUFFERS fabricated with silicon gate and double-layer metal wiring C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

It contains six buffers; four buffers are controlled by an enable input ($\overline{G1}$), and the other two buffers are controlled by another enable input ($\overline{G2}$). The outputs of each buffer group are enabled when $\overline{G1}$ and/or $\overline{G2}$ inputs are held low; if held high, these outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

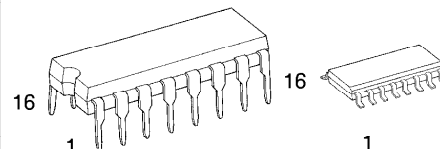
FEATURES:

- High Speed..... $t_{pd} = 3.7\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 8\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}(\text{Min.})$
- Symmetrical Output Impedance... $|I_{OH}| = |I_{OL}| = 24\text{mA}(\text{Min.})$
Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range.... $V_{CC}(\text{opr}) = 2\text{V} \sim 5.5\text{V}$
- Pin and Function Compatible with 74F367

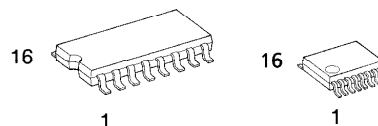
TRUTH TABLE

INPUTS		OUTPUTS
$\overline{G}$	A	Y
L	L	L
L	H	H
H	X	Z

X : Don't Care
Z : High Impedance

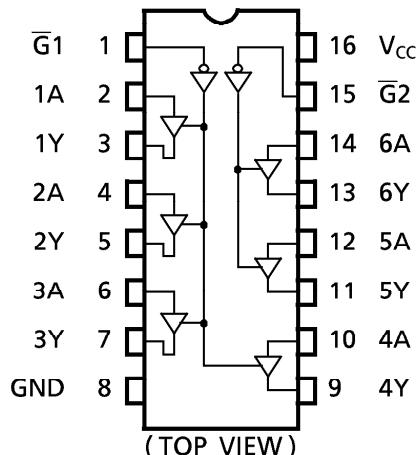


P (DIP16—P—300A) FN (SOL16—P—150)
Weight : 1.00g (TYP.) Weight : 0.13g (TYP.)

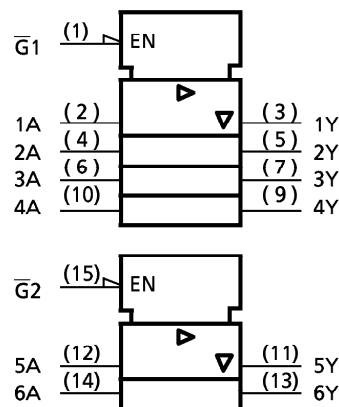


F (SOP16—P—300) FS (SSOP16—P—225B)
Weight : 0.18g (TYP.) Weight : 0.07g (TYP.)

PIN ASSIGNMENT



IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7.0$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /Ground Current	I_{CC}	± 150	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP/SSOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	°C

*500mW in the range of $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$. From $T_a = 65^\circ\text{C}$ to 85°C a derating factor of $-10\text{mW}/^\circ\text{C}$ should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$2.0 \sim 5.5$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	°C
Input Rise and Fall Time	dt/dV	$0 \sim 100$ ($V_{CC} = 3.3 \pm 0.3\text{V}$) $0 \sim 20$ ($V_{CC} = 5 \pm 0.5\text{V}$)	ns/V

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 3.0 5.5	1.50 2.10 3.85	— — —	— — —	1.50 2.10 3.85	— — —	V
Low - Level Input Voltage	V_{IL}		2.0 3.0 5.5	— — —	— — —	0.50 0.90 1.65	— — —	0.50 0.90 1.65	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -50\mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	— — —	1.9 2.9 4.4	V
			$I_{OH} = -4\text{mA}$	3.0	2.58	—	—	2.48	
			$I_{OH} = -24\text{mA}$	4.5	3.94	—	—	3.80	
			$I_{OH} = -75\text{mA}^*$	5.5	—	—	—	3.85	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 50\mu\text{A}$	2.0 3.0 4.5	— — —	0.0 0.0 0.0	0.1 0.1 0.1	— — —	V
			$I_{OL} = 12\text{mA}$	3.0	—	—	—	0.44	
			$I_{OL} = 24\text{mA}$	4.5	—	—	—	0.44	
			$I_{OL} = 75\text{mA}^*$	5.5	—	—	—	1.65	
3 - State Output Off - State Current	I_{oz}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5	—	—	± 0.5	—	± 5.0	μA
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC} \text{ or GND}$	5.5	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC} \text{ or GND}$	5.5	—	—	8.0	—	80.0	

* : This spec indicates the capability of driving 50Ω transmission lines.

One output should be tested at a time for a 10ms maximum duration.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, $R_L = 500\Omega$, Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = − 40~85°C		UNIT
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t _{pLH}		3.3 ± 0.3	—	6.5	11.0	1.0	12.5	ns
	t _{pHL}		5.0 ± 0.5	—	4.5	7.0	1.0	8.0	
Output Enable Time	t _{pZL}		3.3 ± 0.3	—	7.9	13.2	1.0	15.0	
	t _{pZH}		5.0 ± 0.5	—	5.5	8.7	1.0	10.0	
Output Disable Time	t _{pLZ}		3.3 ± 0.3	—	6.3	10.5	1.0	12.0	
	t _{pHZ}		5.0 ± 0.5	—	5.2	7.9	1.0	9.0	
Input Capacitance	C _{IN}			—	5	10	—	10	pF
Output Capacitance	C _{OUT}			—	10	—	—	—	
Power Dissipation Capacitance	C _{PD} (1)			—	28	—	—	—	

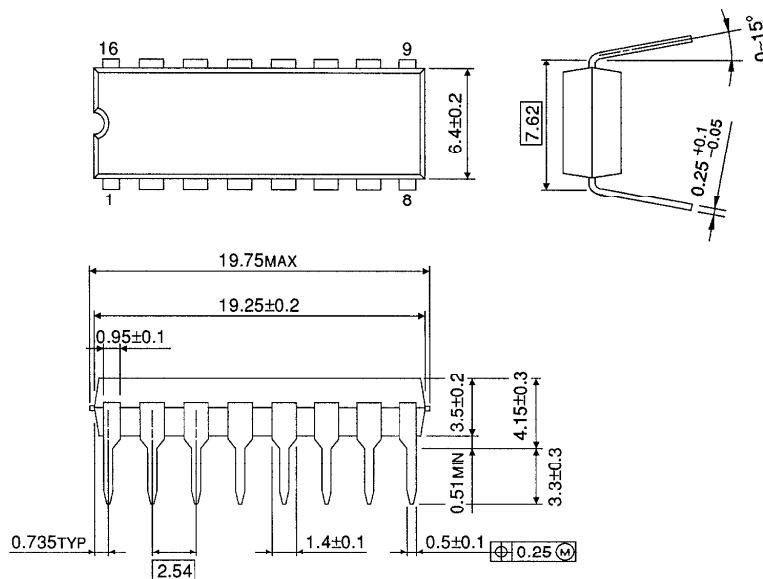
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 6 \text{ (per bit)}$$

DIP 16PIN OUTLINE DRAWING (DIP16—P—300A)

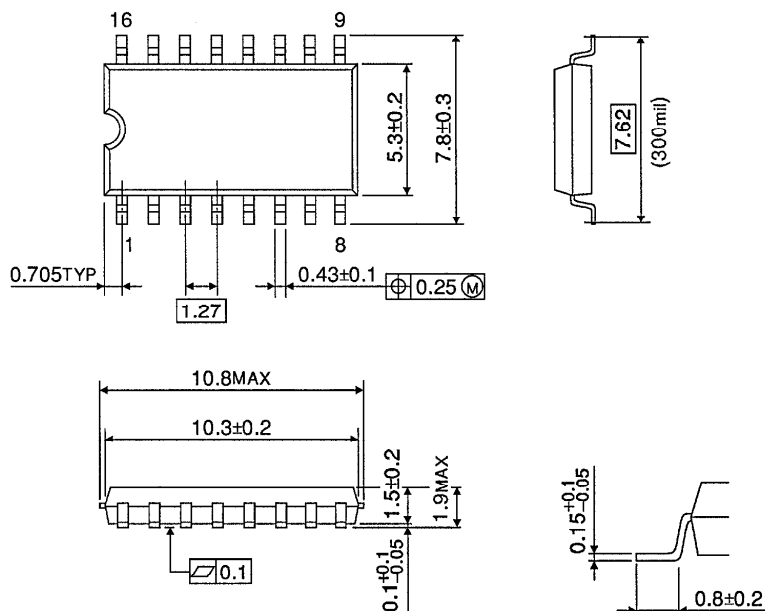
Unit in mm



Weight : 1.00g (TYP.)

SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16—P—300)

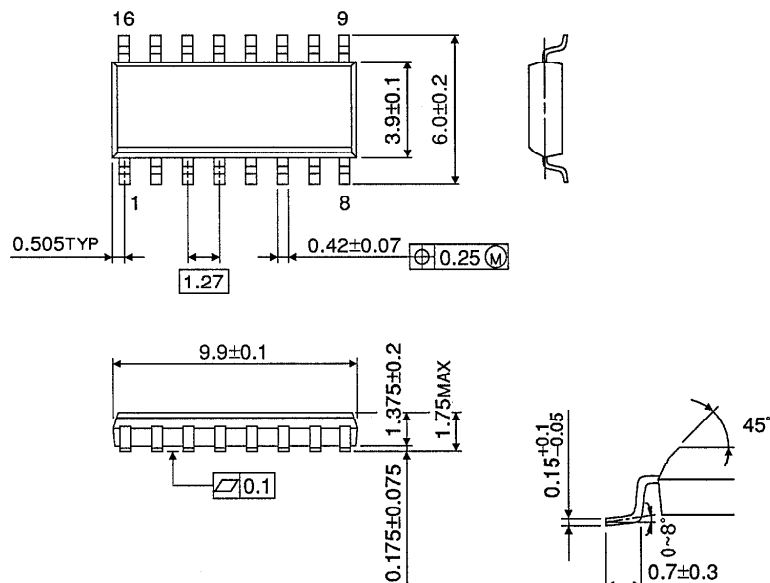
Unit in mm



Weight : 0.18g (TYP.)

SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL16-P-150)

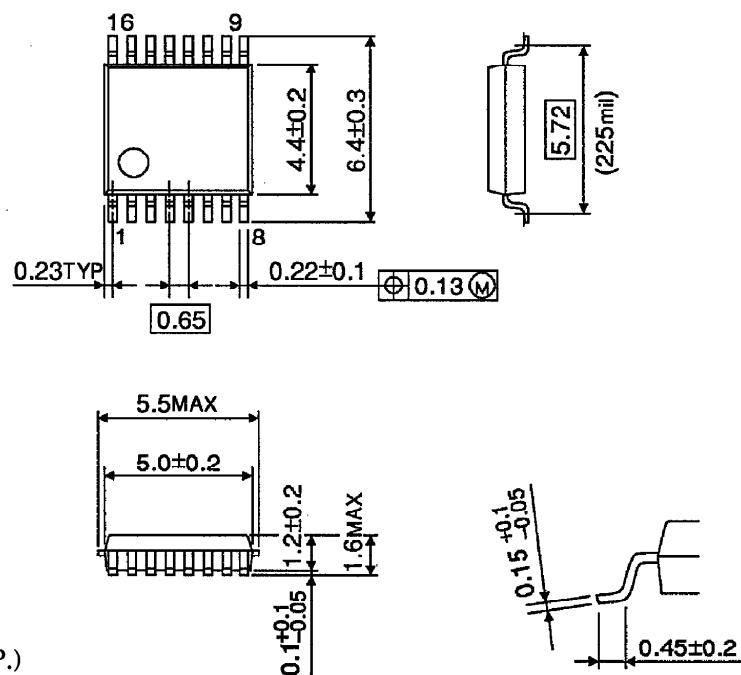
Unit in mm



Weight : 0.13g (TYP.)

SSOP 16PIN OUTLINE DRAWING (SSOP16-P-225B)

Unit in mm



Weight : 0.07g (TYP.)